



Quantitative investigation of group III-nitride interfaces by a combination of scanning tunneling microscopy and off-axis electron holography

Yuhan Wang

Information

Band / Volume 64

ISBN 978-3-95806-534-5

Forschungszentrum Jülich GmbH
Physik Nanoskaliger Systeme (ER-C-1)/
Mikrostrukturforschung (PGI-5)

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Schriften des Forschungszentrums Jülich
Reihe Information / Information

Band / Volume 64

ISSN 1866-1777

ISBN 978-3-95806-534-5

Contents

1	Introduction	5
2	Theoretical and experimental background	9
2.1	Scanning tunneling microscopy	9
2.2	The concept of tunneling	10
2.2.1	One-dimensional model	10
2.2.2	The tunneling current in Bardeen's model	13
2.2.3	The Tersoff-Hamann model	15
2.3	Off-axis electron holography	16
2.3.1	Hologram formation and recording	16
2.3.2	Hologram reconstruction	17
2.3.3	Self-consistent simulations of the phase changes	19
3	Sample description and preparation	21
3.1	The investigated heterostructure	21
3.1.1	Overview of sample	21
3.1.2	Crystal structure of wurtzite structure group III-nitride compounds	22
3.1.3	Composition and doping profiles	24
3.2	Sample and tip preparation for cross-sectional scanning tunneling microscopy	26
3.2.1	Tip preparation	26
3.2.2	Sample preparation	27
3.3	Preparation of lamella for off-axis electron holography	28
4	STM of nitride heterostructure	31
4.1	Topography of the cross-sectional cleavage surface	31
4.2	STS of the ternary nitride layers	33
4.2.1	Experimental results	33
4.2.2	Discussion of the tunneling spectra of m plane group III-nitride surfaces	34
4.3	STS at interfaces	45
4.3.1	Experimental results	45
4.3.2	Discussion of tunneling spectra at interfaces	51

4.4 Conclusions	51
5 Quantitative determination of electrical properties of semiconductor interfaces by off-axis electron holography	53
5.1 Experimental results	53
5.2 Discussion	57
5.2.1 Comparison of holography with SIMS and STM	57
5.2.2 Theoretical discussion of electron holography	58
5.2.3 Comparison with self-consistent simulations	60
5.2.4 Discussion of the effect of surface Fermi-level pinning, electron affinity change, MIP change, and polarization change on the phase shift	67
5.3 Conclusions	71
6 Interplay of lattice strain and electronic properties at heterointerfaces	73
6.1 Lattice constants and strain	73
6.2 Derivation of the MIP values for strained ternary group III nitrides	77
6.3 Electron affinity changes	78
6.3.1 Without strain	78
6.3.2 With strain	79
6.4 Polarization changes	81
6.4.1 Without strain	81
6.4.2 With strain	81
6.5 Discussion	82
6.6 Conclusions	84
7 Summary	85
Bibliography	89
Acknowledgement	101

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